

## Silicon PNP Power Transistors

2SA634

## DESCRIPTION

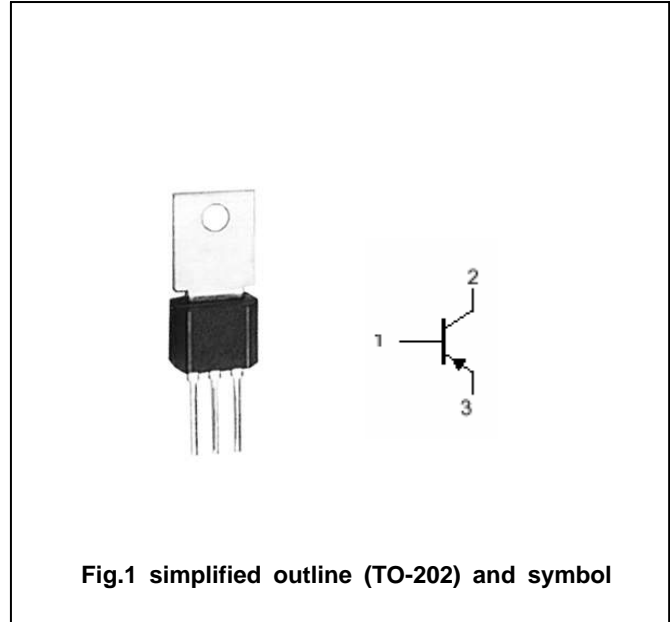
- With TO-202 package
- Complement to type 2SC1096
- High current capability

## APPLICATIONS

- Audio frequency power amplifier
- Low speed switching

## PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-40	V
$V_{CEO}$	Collector-emitter voltage	Open base	-30	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-3.0	A
$I_{CM}$	Collector current-peak		-6.0	A
$I_B$	Base current		-0.6	A
$P_T$	Total power dissipation	$T_a=25^\circ\text{C}$	1.2	W
		$T_c=25^\circ\text{C}$	10	
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3.0A ; I <sub>B</sub> =-0.3 A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3.0A ; I <sub>B</sub> =-0.3 A			-2.0	V
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA ; I <sub>B</sub> =0	-30			V
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-20mA ; V <sub>CE</sub> =-5V	20			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A ; V <sub>CE</sub> =-5V	40		250	
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-30V ; I <sub>E</sub> =0			-1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V ; I <sub>C</sub> =0			-1.0	μ A
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V ; f=1MHz		75		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A ; V <sub>CE</sub> =-5V		55		MHz

◆ h<sub>FE-2</sub> Classifications

N	M	L	K
40-60	50-100	80-160	120-250

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PACKAGE OUTLINE

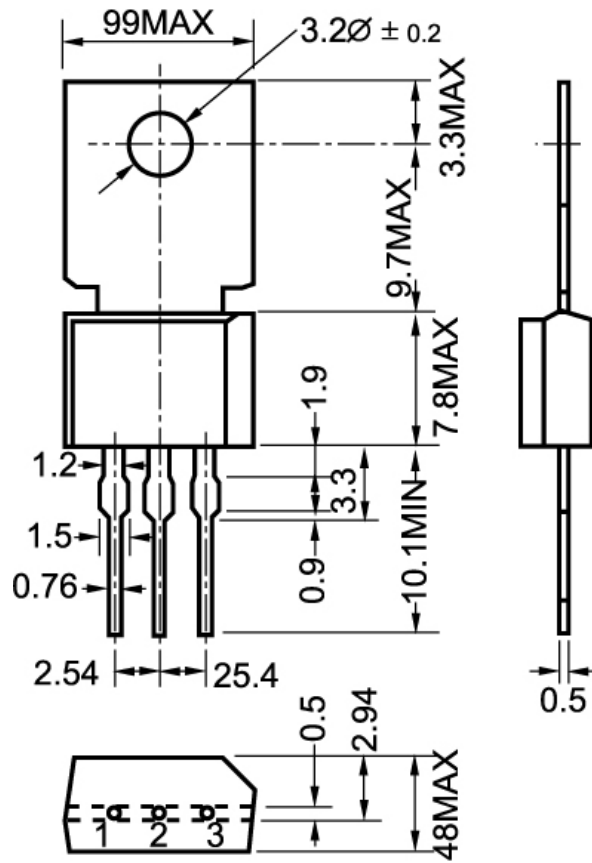


Fig.2 outline dimensions